

# YJ Planar Schottky Barrier Diode Die Specification

150V 1A, 32mil, Schottky barrier diode die based on silicon planar process  
Part No.: PSB032H150SS-280A

## Main Products Characterstics

‡ \$YHUDJH IRUZDUG FXUUHQW ,) \$9 \$  
‡ 0D[LPXP RSHUDWLQJ MXQFWLRQ WHPSHUDWXUH 7M f &  
‡ (6' UDWLQJ !.9 SHU ,(& &RQWDFW 'LVFKDUJH  
‡ 7RS PHWDO \$J

## Maximum Ratings

## Static Electrical Characteristics (Ta = 25°C)

$I_F = 1\text{ A}$   
 $3 \times 0 \text{ V H } 7 \text{ H V W } \text{ W } \leq 2\%$

## Device Schematics and Outline Drawing

Die Thickness \*  
Die Size \*\*  
Top Metal Pad  
Active Area  
Top Metal  
Back Metal  
Note: 1 \* : Also can offer device with 8 mils thickness  
2 \*\*: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.  
Recommended Storage Environment:  
does not guarantee device performance after assembly.  
Store in original container, in dessicated nitrogen, with no contamination.  
Operating temperature range: -55°C to 175°C (x-none)  
BDC 0916 71f1tID 25reWhBTf3 6.72 Tf1 0 0 1 0 1m3 6.7 0 0 bce th noblyno